2020 Technology Briefing

Scott DeBoer, EVP

November 30, 2020

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Scott DeBoer

Executive Vice President
Technology and Products

The New Micron's Journey

Closing the Gap

2016-2020

- Faster node transitions
- Investments towards vertical integration and scale
- Build quality leadership
- Grow high value solutions mix
- Supply growth in line with demand

Technology & Product Leadership

2021+

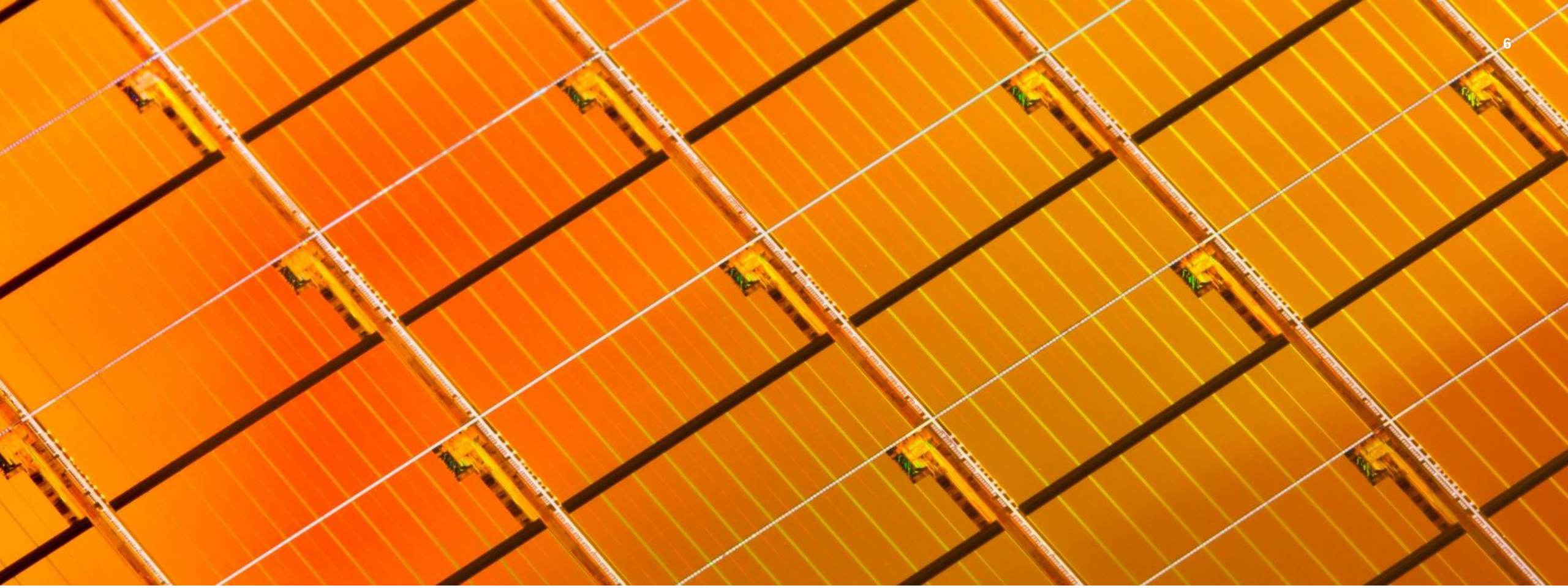
- Introduce leading tech nodes at a typical industry cadence, while maintaining our improved competitive position
- Differentiated solutions ready for heterogenous computing architectures
- Supply growth in line with demand

Agenda

Strategy

Technology

Product



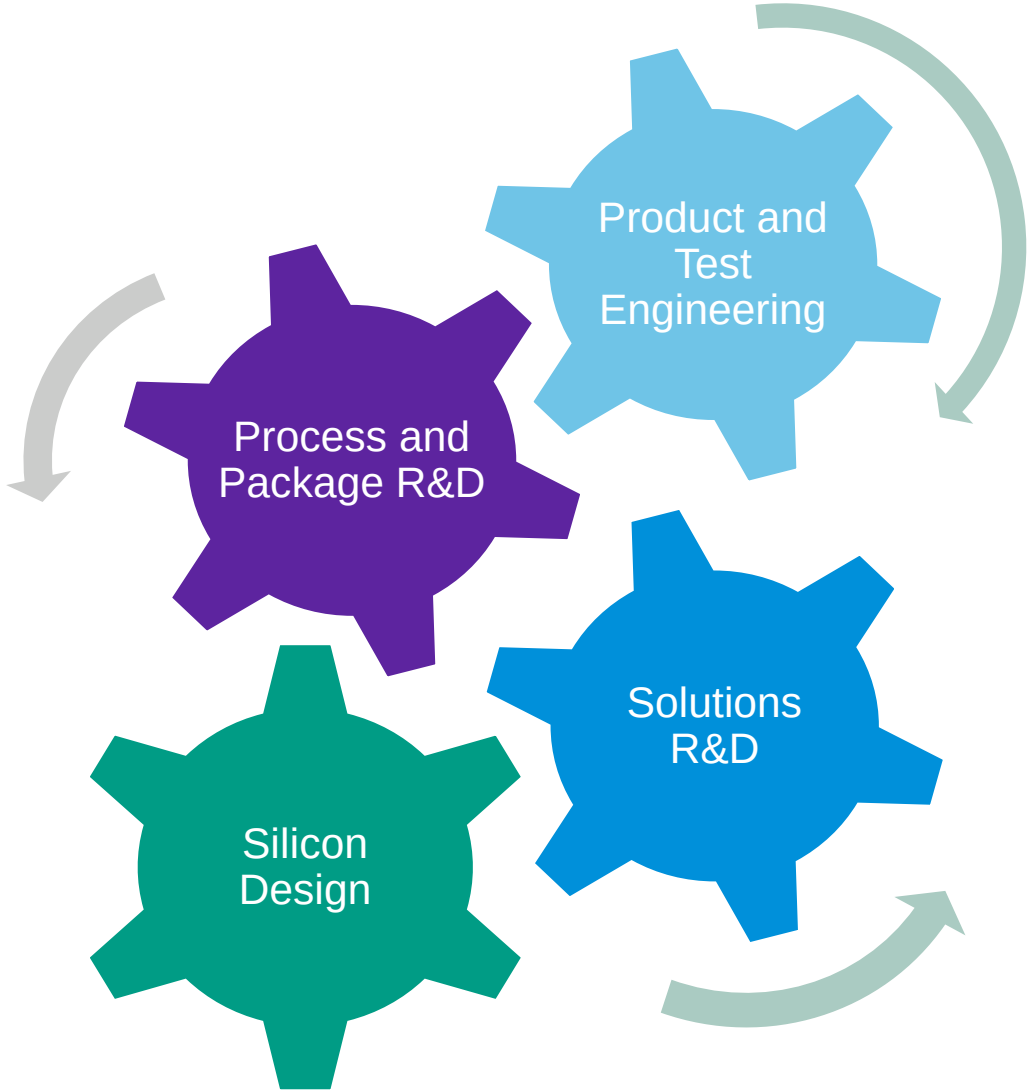
Strategy

The New Micron is Strong and Getting Stronger

R&D Efficiency	Broadest Portfolio	Team & Culture

Integration of Technology & Product

Enables greater R&D efficiency and customer value creation



- **Time to Market**
- **Differentiated Performance**
- **Best-in-Class Quality**
- **Cost Competitiveness**

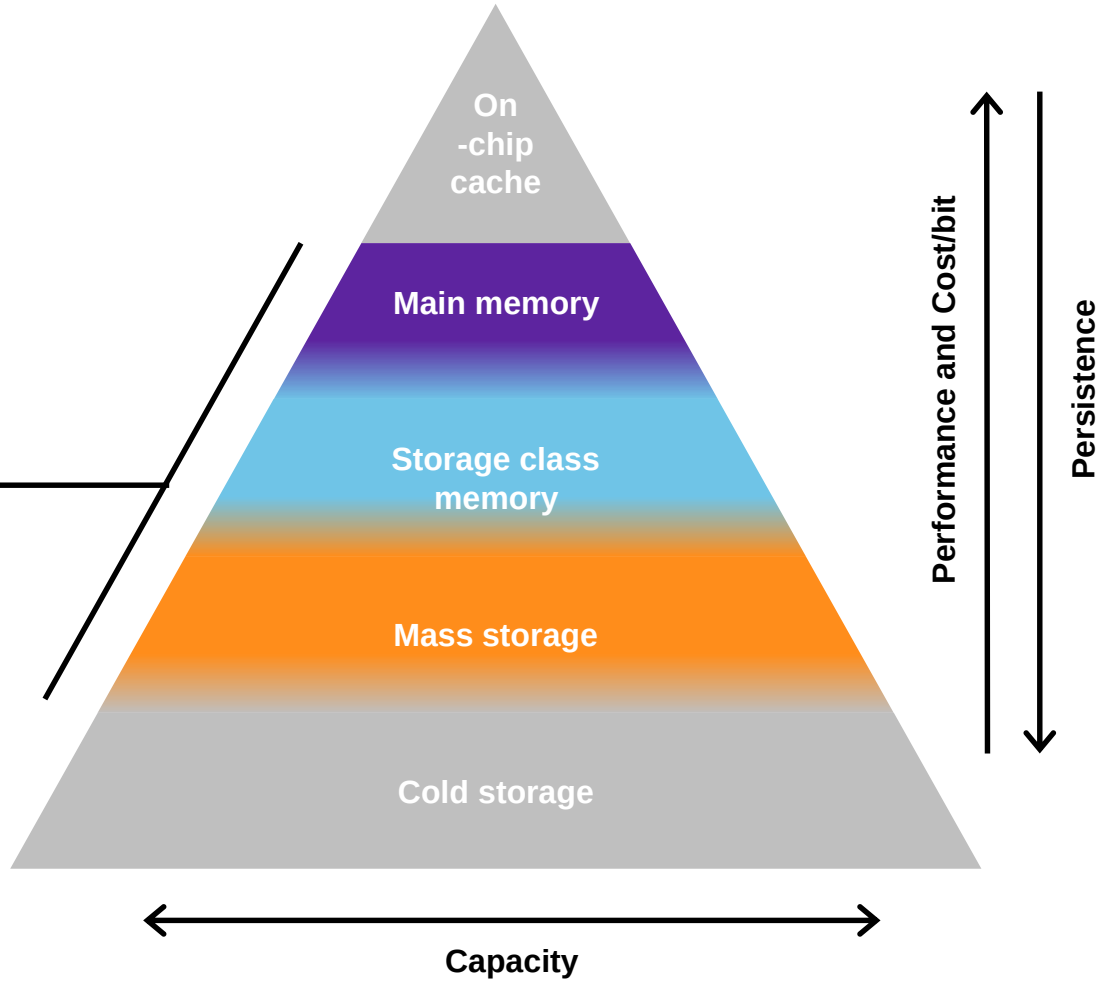
Industry's Broadest Portfolio

Ability to leverage core technology across the memory and storage hierarchy

DRAM
Ultra-Bandwidth: HBM2E, GDDR6X
Compute: DDR5
Mobile: Low power leadership

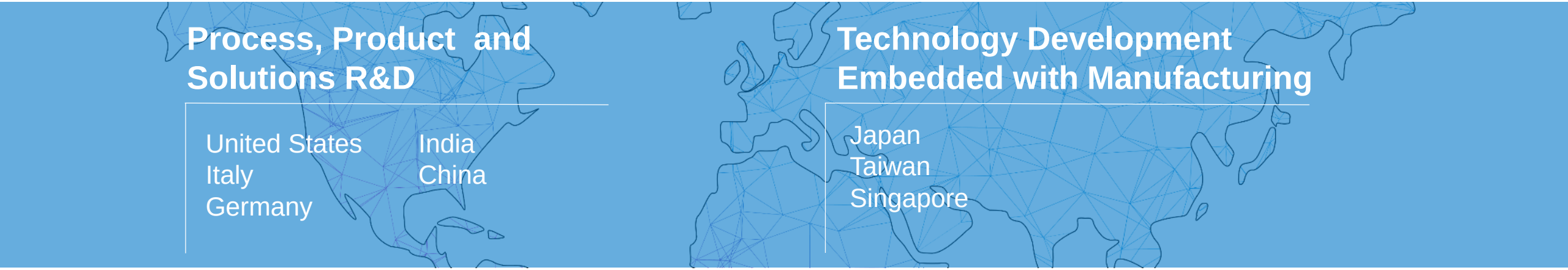
3DXP
Memory: Future development
Storage: X100 – world's fastest SSD

NAND
Managed NAND: UFS3.1/2.x, uMCP5
SSD: Client, Datacenter NVMe/SATA
QLC: HDD replacement trajectory



Team & Culture

Uniquely positioned to attract the industry's best global talent



Team

- Global talent fuels innovation
- >50% of R&D new hires with MS, PhD
- >60% technical with industry experience
- Strong talent pipeline, engaged with top global universities

Culture

- Team Member Health & Safety
- Excellence in Execution
- Certified 2020 Great Place to Work
- Forbes 2020 "The Best Employer for Diversity"
- Focus on Environmental Sustainability

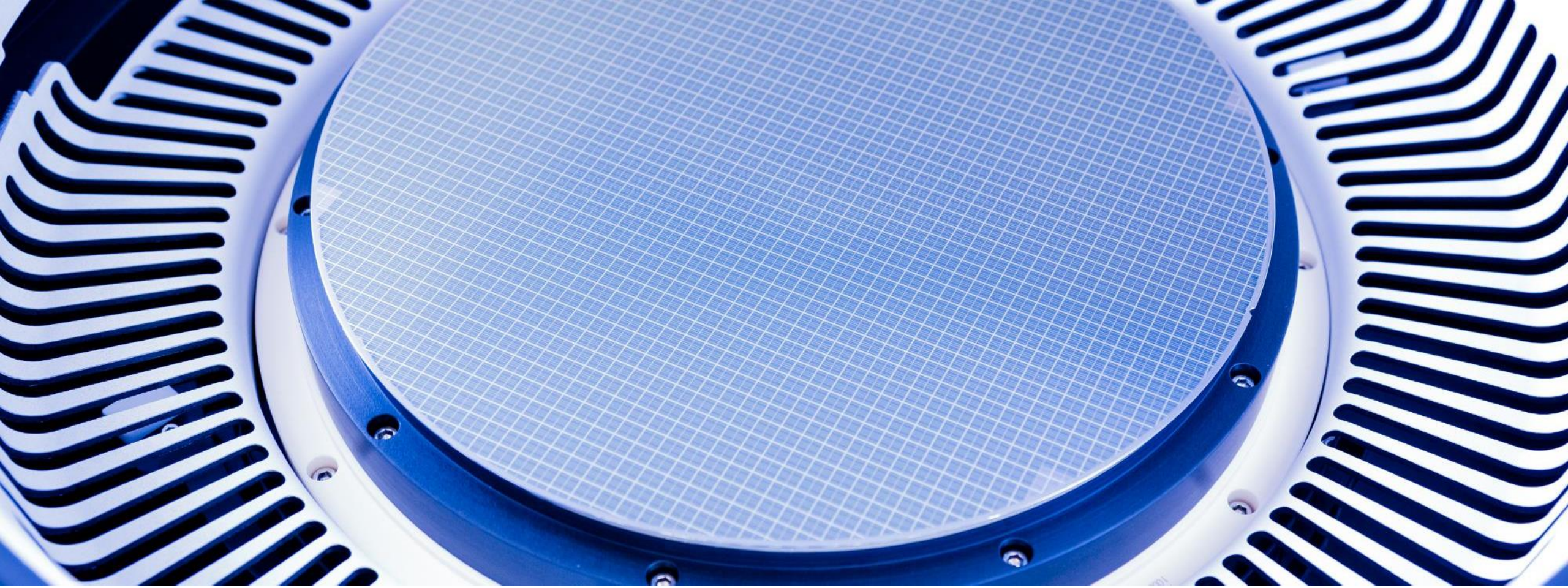
Learn more: August 24, 2020 Sustainability Update

Innovation

- Over 44,000 patents granted and growing*
- Top 25 on US Patent list
- Micron Women Innovate program

*Micron data as of September 3, 2020.

Technology

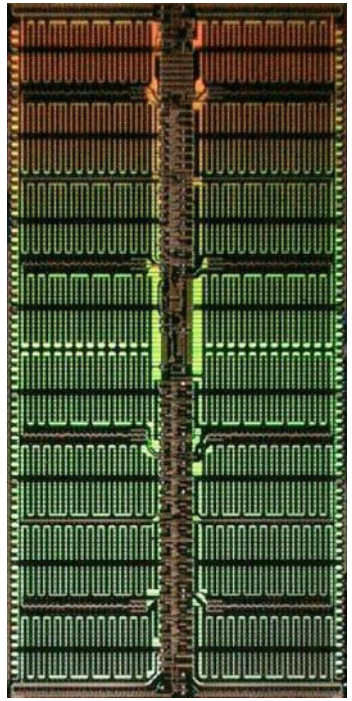


Technology

DRAM

1α nm: Industry's Most Advanced DRAM

Volume production in 1H-CY21



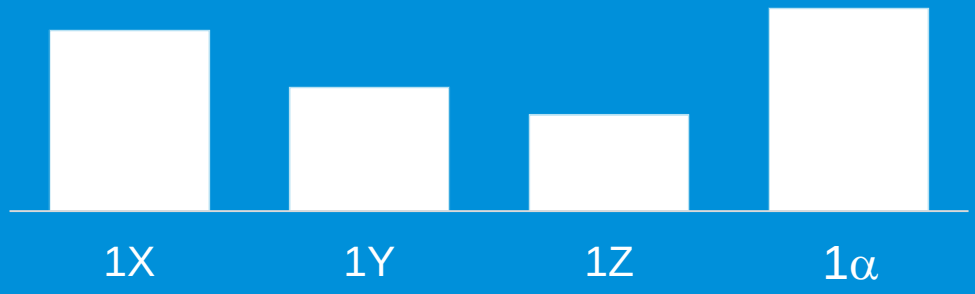
1αnm DRAM: 8Gb DDR4

- ✓ Lowest power mobile DRAM with 15% improvement vs. prior gen
- ✓ Roadmap for highest speed DRAM available across comprehensive portfolio

Achieved with Leading Design Efficiency and Process Technology

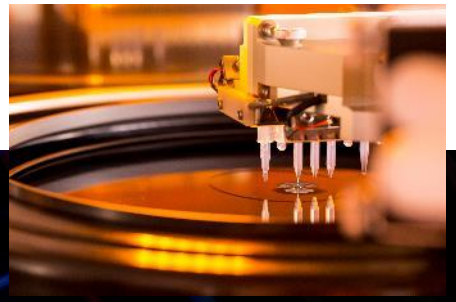
- ✓ Industry's most advanced lithography
- ✓ **40%** improvement in density vs. 1Z with **~10%** driven by design efficiency

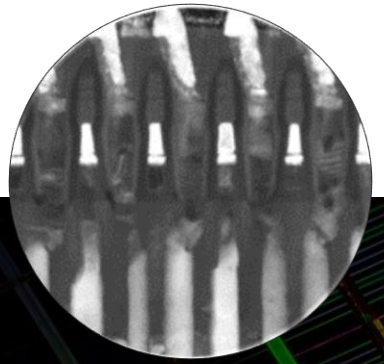
DDR4 % Gb/Wafer Increase from Prior Node

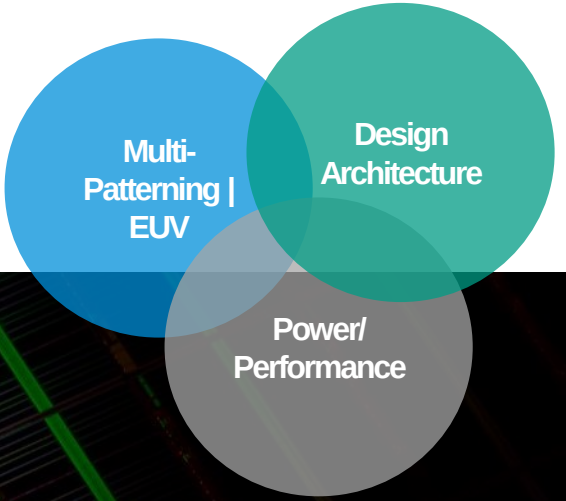


DRAM Technology Leadership

Continuing to extend roadmap for cost and performance improvement







1α Customer Qualification

1β Early Development

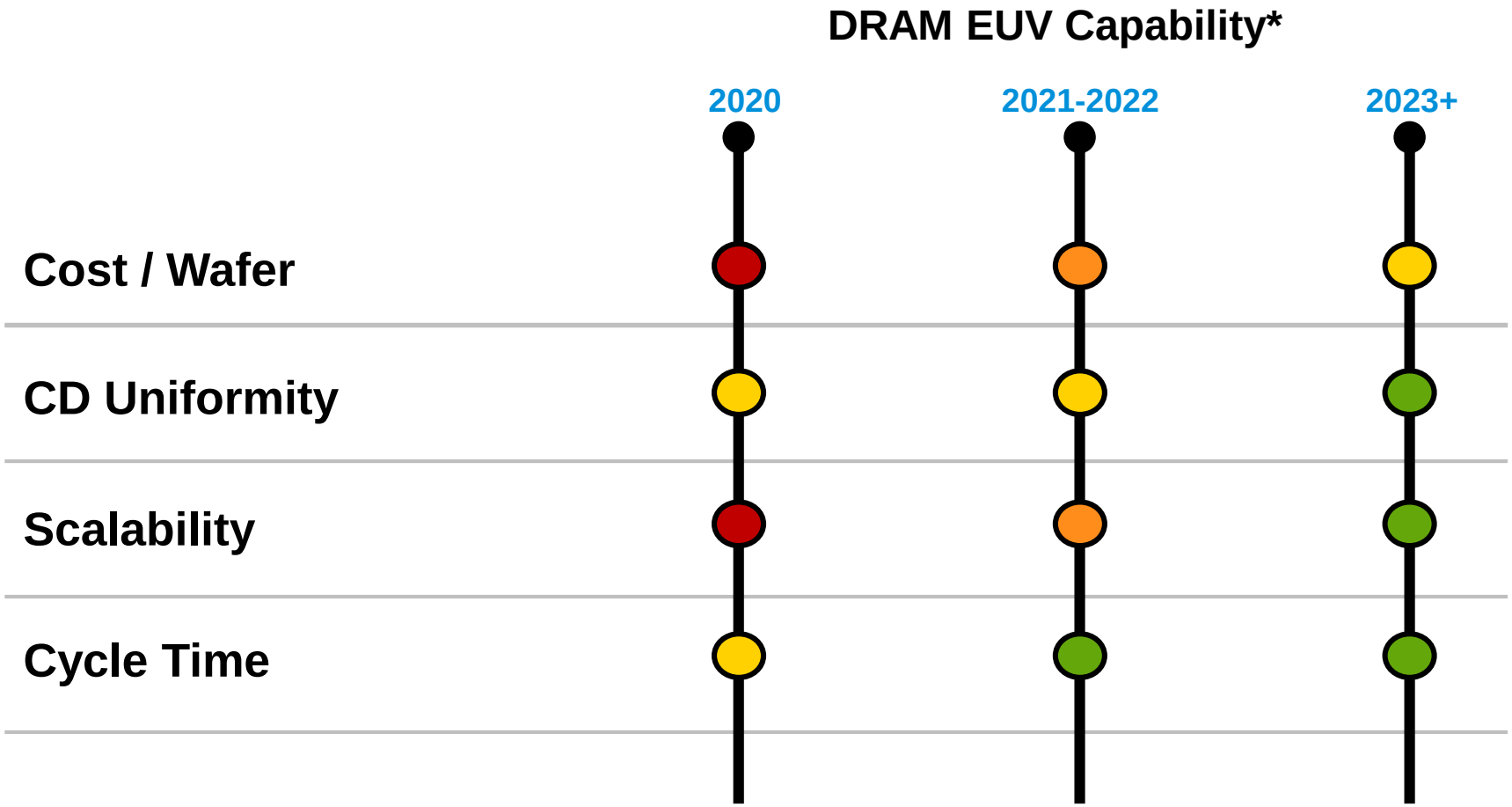
1γ Early Process Integration

1δ Pathfinding

- Path for continued scaling over the next decade
- High performance/low power transistor roadmap enabled by High-κ CMOS
- Continued evaluation of EUV for cost optimized insertion

DRAM EUV Performance Improving

Potential future option for Micron DRAM lithography



*Micron Performance analysis relative to Micron DRAM requirements

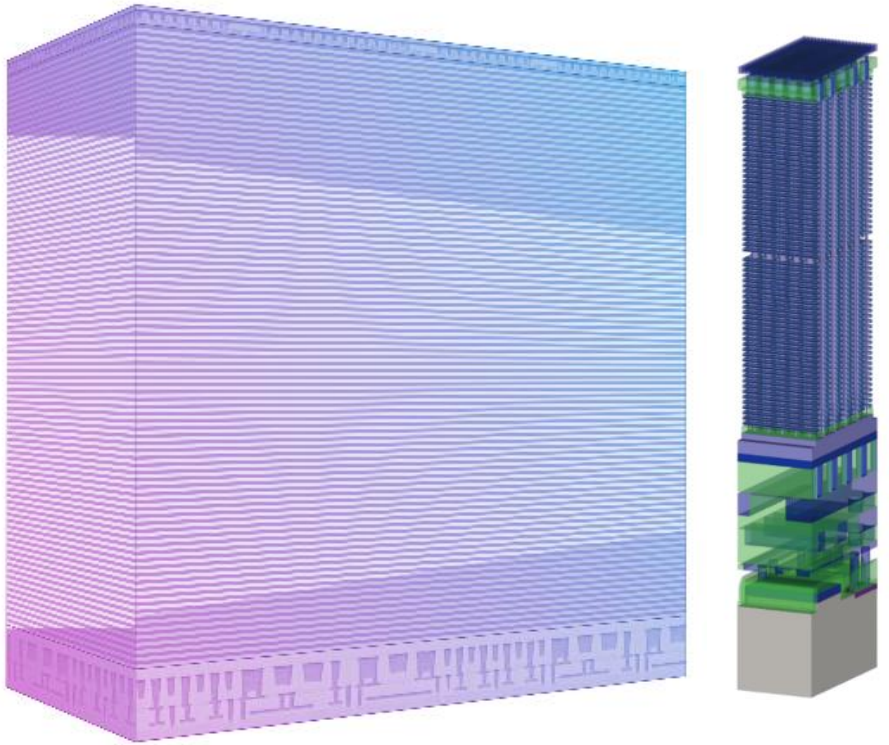
Technology

NAND

The World's First 176-Layer NAND

Innovation driving breakthrough speed, power efficiency and density

- ✓30% smaller die size than best-in-class competitive offerings
- ✓~1.5x cost reduction vs. 64L/96L transition*
- ✓>2x improved power efficiency†
- ✓>2x better write times†
- ✓33% higher data transfer rate†



Dual stack

*Cash cost per Gb vs. 64L/96L transition

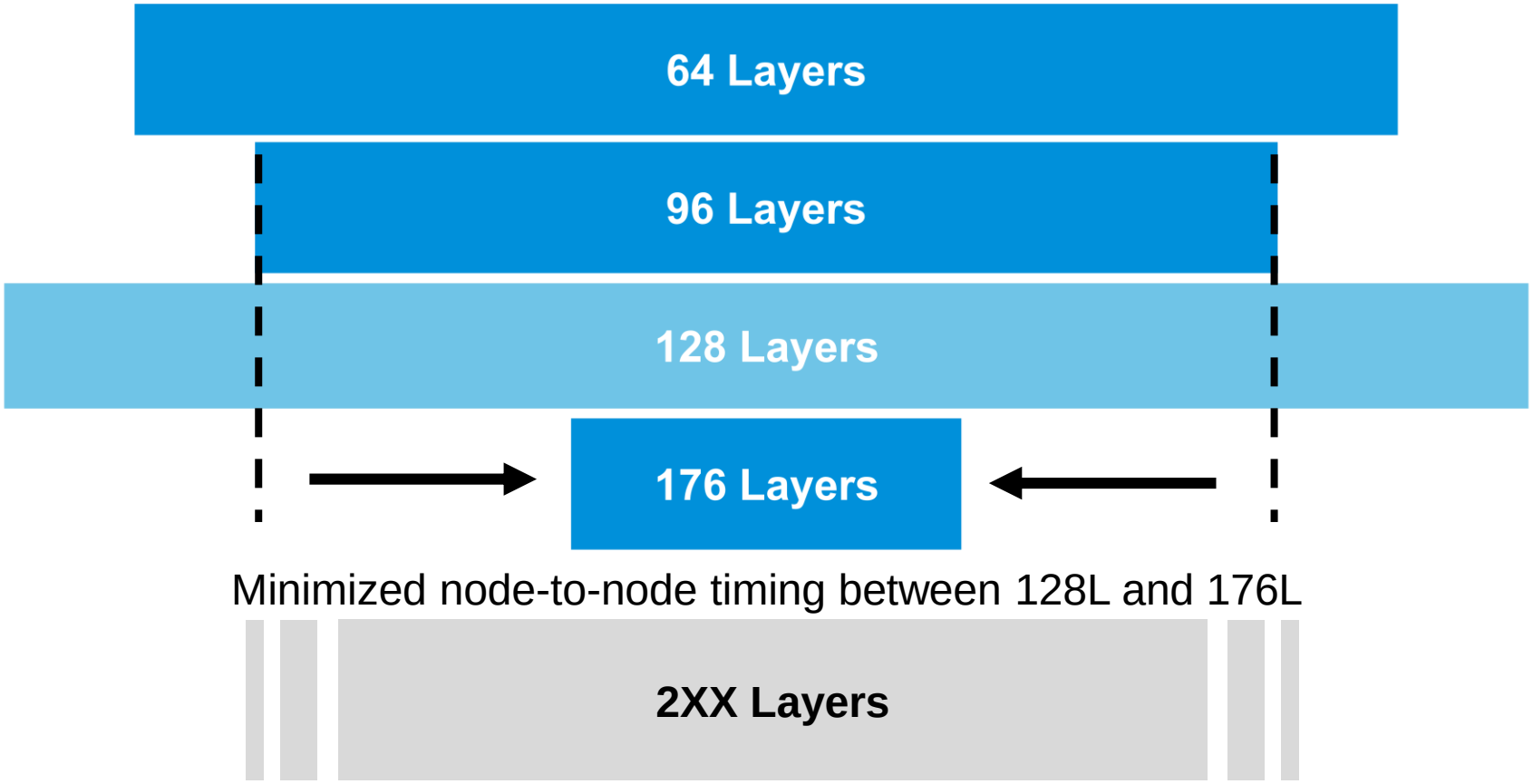
†versus Micron's high volume, floating-gate 96-Layer 3D NAND

Learn more here on micron.com

Accelerating Time to Market for 176 Layer

Successful replacement gate (RG) transition enables industry leadership

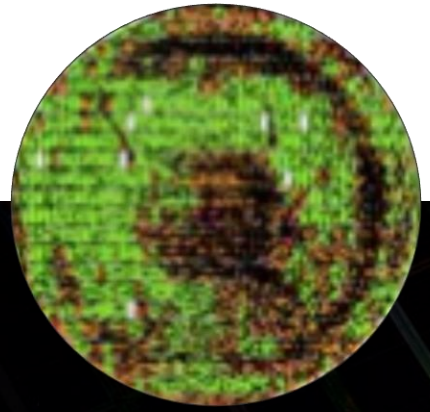
NAND



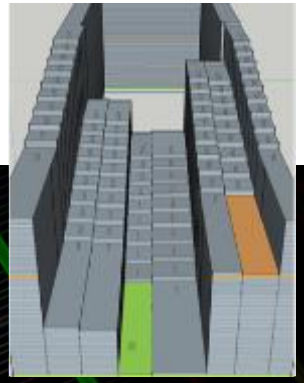
NAND Technology Leadership

Continuing to extend roadmap for cost and performance improvement

176 Layer RG
Volume Production



2XX Layer RG
Yield Enablement



Next Gen. RG
Early Development

- Continued 3D NAND scaling and cost reductions for several generations
- Combination of replacement gate (RG), charge trap and CMOS under Array delivers performance leadership
- Extend QLC performance leadership

Replacement Gate

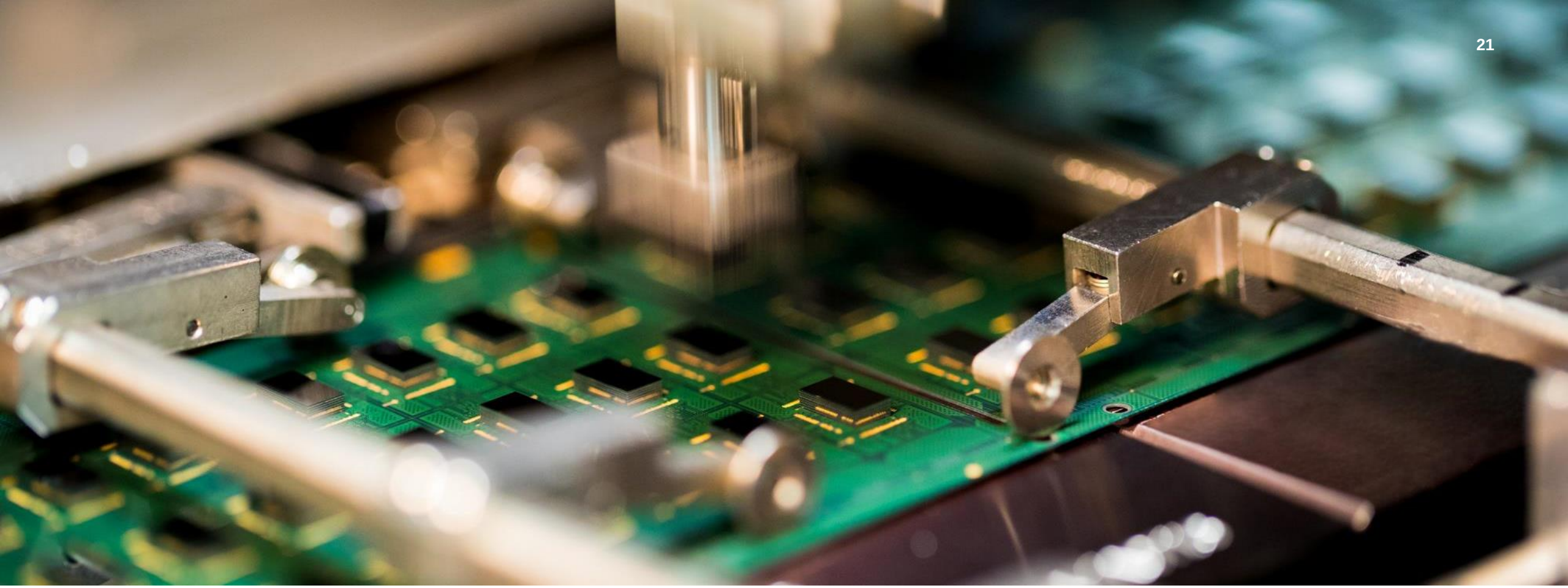
Driving scalability and performance for 3D NAND generations to come

Attribute	<100 Layers		>100 Layers	
	Floating Gate	Replacement Gate	Floating Gate	Replacement Gate
Cost Scalability				
Power				
Performance				
Retention				
Endurance				
QLC Compatibility				

FG made sense for <100 layers

RG is superior for >100 layers

Note: Gradient indicates change over node transitions



Product

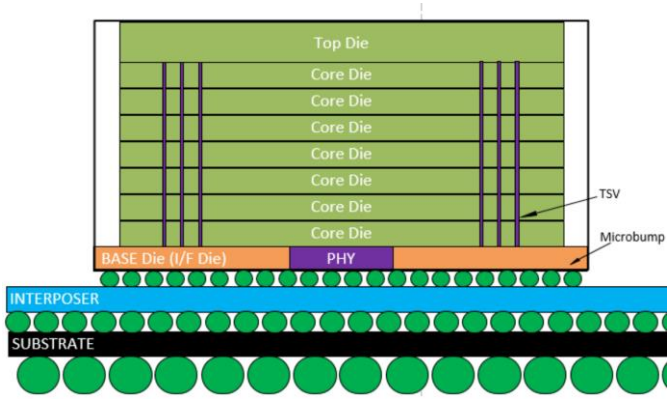
Broadest Portfolio of Memory and Storage Products

Ultra-Bandwidth Solutions	Mobile Leadership	SSD Leadership

Ultra-Bandwidth Solutions for AI Training and Inference from Edge to Cloud

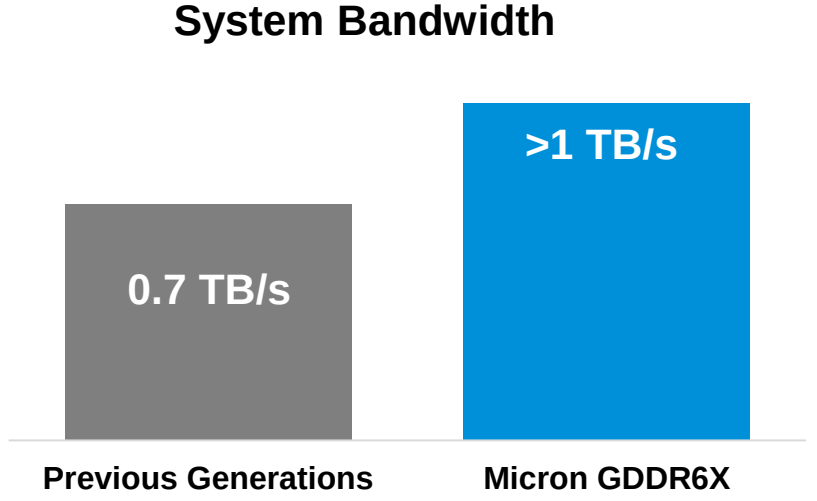
HBM2E: AI Training & Inference for Cloud

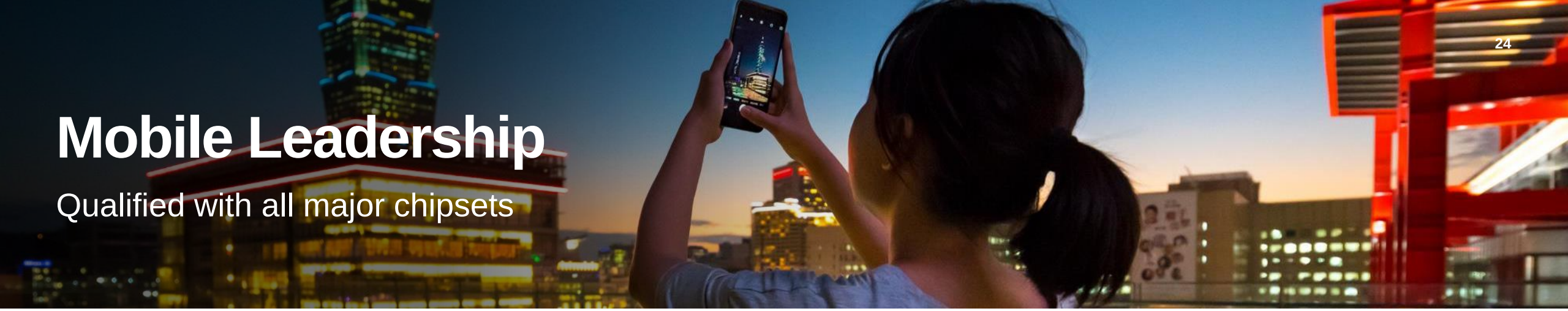
- Enabling system bandwidth >2 TB/s
- Shipping to Customers
- >20 years of experience in stacked TSV memory with thousands of patents



GDDR6X: AI Inference for Edge

By using PAM4 multi-level signaling, Micron GDDR6X transfers more data at a much faster rate, moving two bits of information at a time, doubling the I/O data rate.





Mobile Leadership

Qualified with all major chipsets

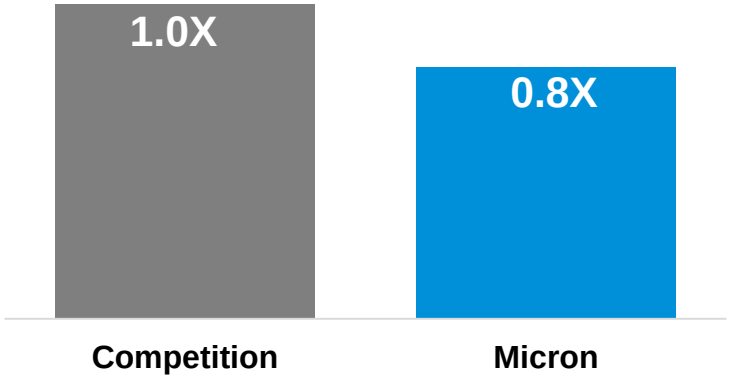
Memory
LPDDR5, LPDDR4x

Storage Solutions
UFS3.1, UFS2.x, eMMC

Multichip Packages (MCPs)
uMCP5, uMCP4x, eMCP4x

Leveraging low power DRAM and NAND technology leadership

LP5 Power Consumption
8k Video Recording
(lower = better)



Competition refers to LP5 products offered by our industry competitors

Redefining the End-User Experience

- AI & machine learning
- Rapid high-resolution photo/video capture
- Longer battery life
- Shorter app launch times
- Multi-tasking capability

Broad SSD Portfolio

Spanning cost, performance and end-markets

Datacenter
NVMe, SATA leader,
QLC, X100

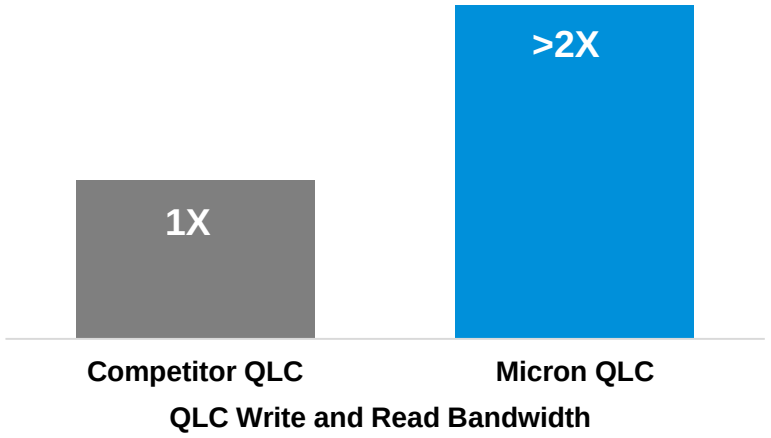
Client
NVMe, SATA, QLC

Auto
Specialized NVMe BGA SSD

Leveraging 176 Layer leadership

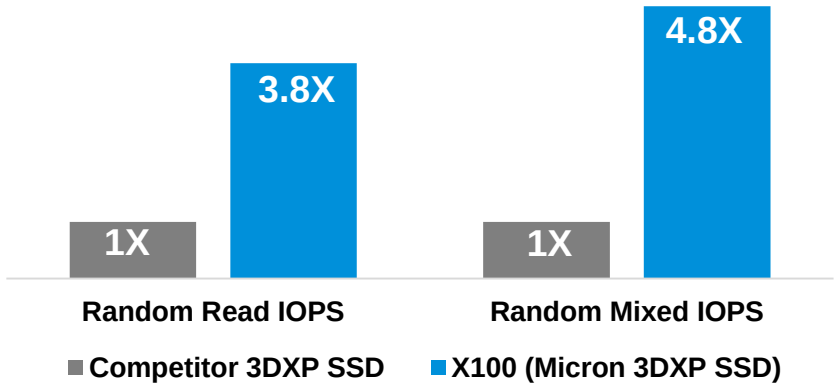
Using a growing mix of internally developed controllers

QLC Performance Leadership
(higher = better)



QLC leadership accelerating opportunity for HDD replacement

Breakthrough Performance with 3DXP
(higher = better)



X100 – world's fastest SSD pushing the frontier of possibilities

Transforming how the world uses information to enrich life *for all.*

Industry’s leading technology for DRAM and NAND

Industry’s broadest portfolio, driving to deliver product leadership

Partnering with customers to unleash the value of data for all

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